

MGFC40V5258

5.2~5.8GHz BAND 10W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC40V5258 is an internally impedance-matched GaAs power FET especially designed for use in 5.2~5.8 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

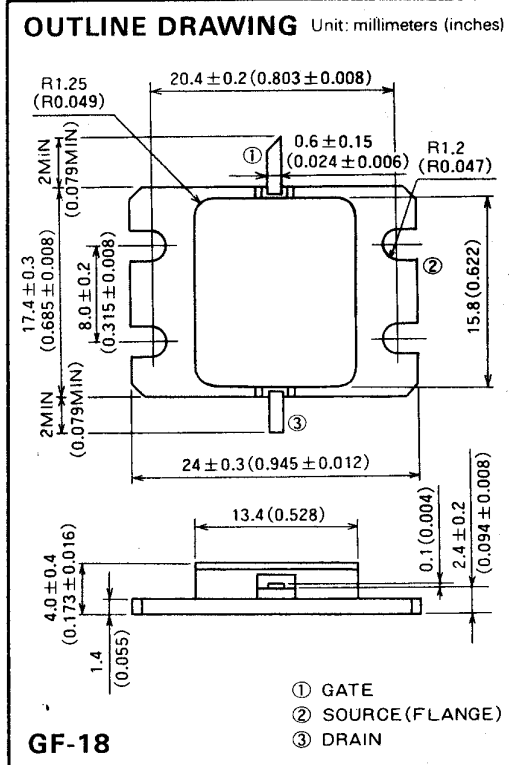
- Class A operation
- Internally matched to 50Ω system
- High output power
 $P_{1dB} = 10W$ (TYP) @ 5.2~5.8 GHz
- High power gain
 $G_{LP} = 9$ dB (TYP) @ 5.2~5.8GHz
- High power added efficiency
 $\eta_{add} = 32\%$ (TYP) @ 5.2~5.8 GHz, P_{1dB}
- Hermetically sealed metal-ceramic package

APPLICATION

- Item-01: 5.2~5.8GHz band power amplifier
- Item-51: Digital radio communication

QUALITY GRADE

- IG



RECOMMENDED BIAS CONDITIONS

- $V_{DS} = 10V$
- $I_D = 2.4A$
- $R_g = 50\Omega$
- Refer to Bias Procedure

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

| Symbol | Parameter | Ratings | Unit |
|-----------|----------------------------|------------|------|
| V_{GDO} | Gate to drain voltage | -15 | V |
| V_{GSO} | Gate to source voltage | -15 | V |
| I_D | Drain current | 6 | A |
| I_{GR} | Reverse gate current | -20 | mA |
| I_{GF} | Forward gate current | 42 | mA |
| P_T | Total power dissipation *1 | 42.8 | W |
| T_{ch} | Channel temperature | 175 | °C |
| T_{stg} | Storage temperature | -65 ~ +175 | °C |

*1: $T_c = 25^\circ C$

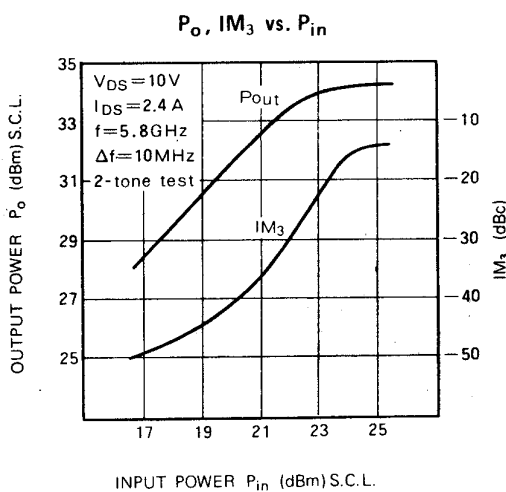
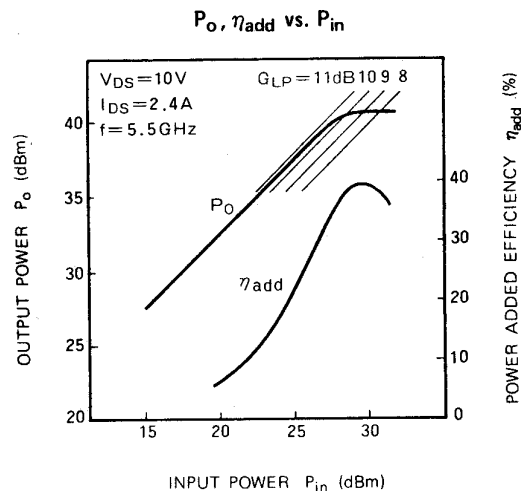
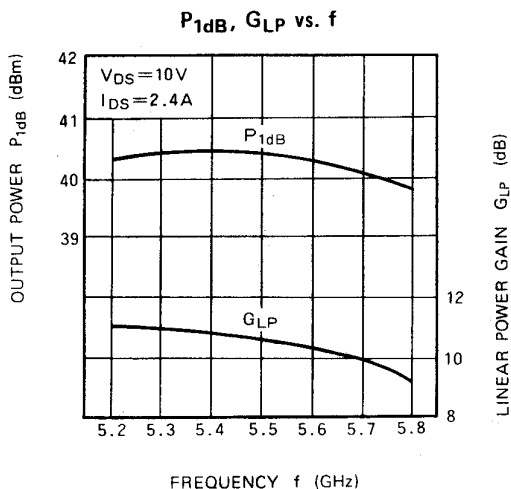
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

| Symbol | Parameter | Test conditions | Limits | | | Unit | |
|----------------|--------------------------------------|---|---------------------|------|-----|------|------|
| | | | Min | Typ | Max | | |
| I_{DSS} | Saturated drain current | $V_{DS} = 3V, V_{GS} = 0V$ | — | 4.5 | 6 | A | |
| g_m | Transconductance | $V_{DS} = 3V, I_D = 2.2A$ | — | 2 | — | S | |
| $V_{GS(off)}$ | Gate to source cut-off voltage | $V_{DS} = 3V, I_D = 40mA$ | -2 | -3 | -4 | V | |
| P_{1dB} | Output power at 1dB gain compression | $V_{DS} = 10V, I_D = 2.4A, f = 5.2 \sim 5.8GHz$ | 39.5 | 40.5 | — | dBm | |
| G_{LP} | Linear power gain | | 8 | 9 | — | dB | |
| I_D | Drain current | | — | 2.4 | — | A | |
| η_{add} | Power added efficiency | | — | 32 | — | % | |
| $R_{th(ch-c)}$ | Thermal resistance *1 | | ΔV_f method | — | — | 3.5 | °C/W |

*1: Channel to case

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TYPICAL CHARACTERISTICS



S PARAMETERS ($T_a=25^\circ C$, $V_{DS}=10V$, $I_{DS}=2.4A$)

| f (GHz) | S Parameters (TYP.) | | | | | | | |
|------------|---------------------|--------------|-------|--------------|-------|--------------|-------|--------------|
| | S11 | | S21 | | S12 | | S22 | |
| | Magn. | Angle (deg.) | Magn. | Angle (deg.) | Magn. | Angle (deg.) | Magn. | Angle (deg.) |
| 5.2 | 0.40 | -170.9 | 3.56 | 34.3 | 0.071 | -24.8 | 0.32 | -134.4 |
| 5.3 | 0.41 | 140.3 | 3.53 | -6.5 | 0.072 | -65.4 | 0.31 | -171.2 |
| 5.4 | 0.40 | 92.6 | 3.50 | -47.4 | 0.073 | -106.6 | 0.29 | -155.1 |
| 5.5 | 0.39 | 41.3 | 3.43 | -88.0 | 0.073 | -147.2 | 0.26 | 123.6 |
| 5.6 | 0.40 | -15.1 | 3.27 | -129.5 | 0.073 | 171.2 | 0.21 | 95.4 |
| 5.7 | 0.44 | -76.5 | 3.16 | -173.5 | 0.071 | 127.6 | 0.14 | 77.0 |
| 5.8 | 0.49 | -100.0 | 2.92 | 173.5 | 0.071 | 83.0 | 0.13 | 69.0 |